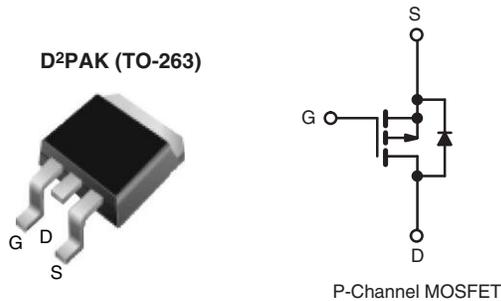


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 100	
$R_{DS(on)}$ (Ω)	$V_{GS} = - 10$ V	0.30
Q_g (Max.) (nC)	38	
Q_{gs} (nC)	6.8	
Q_{gd} (nC)	21	
Configuration	Single	



FEATURES

- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- 175 °C Operating Temperature
- Fast Switching
- Lead (Pb)-free Available


 Available
RoHS*
 COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²PAK (TO-263) is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION			
Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free	IRF9530SPbF	IRF9530STRLPbF ^a	IRF9530STRRPbF ^a
	SiHF9530S-E3	SiHF9530STL-E3 ^a	SiHF9530STR-E3 ^a
SnPb	IRF9530S	IRF9530STRL ^a	IRF9530STRR ^a
	SiHF9530S	SiHF9530STL ^a	SiHF9530STR ^a

Note

- a. See device orientation.

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	- 48	
Linear Derating Factor		0.59	W/°C
Linear Derating Factor (PCB Mount) ^e		0.025	
Single Pulse Avalanche Energy ^b	E_{AS}	400	mJ
Avalanche Current ^a	I_{AR}	- 12	A
Repetitive Avalanche Energy ^a	E_{AR}	8.8	mJ
Maximum Power Dissipation	P_D	$T_C = 25$ °C	88
Maximum Power Dissipation (PCB Mount) ^e		$T_A = 25$ °C	3.7
Peak Diode Recovery dV/dt ^c	dV/dt	- 5.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	

Notes

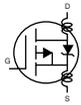
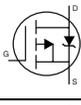
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = - 25$ V, starting $T_J = 25$ °C, $L = 4.2$ mH, $R_G = 25$ Ω , $I_{AS} = - 12$ A (see fig. 12).
- $I_{SD} \leq - 12$ A, $di/dt \leq 140$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note

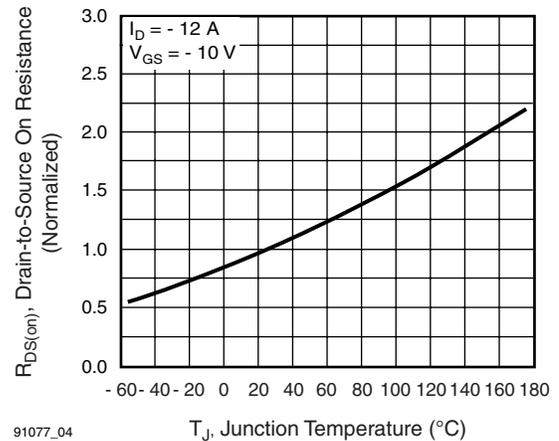
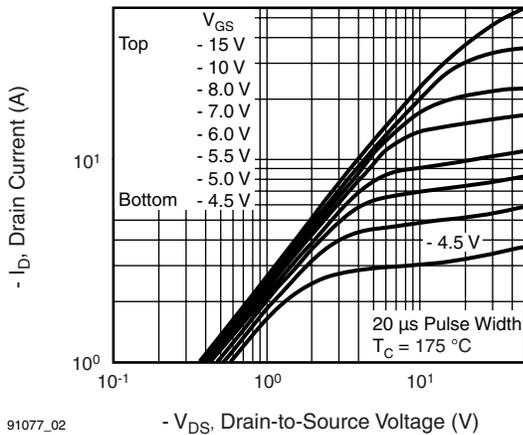
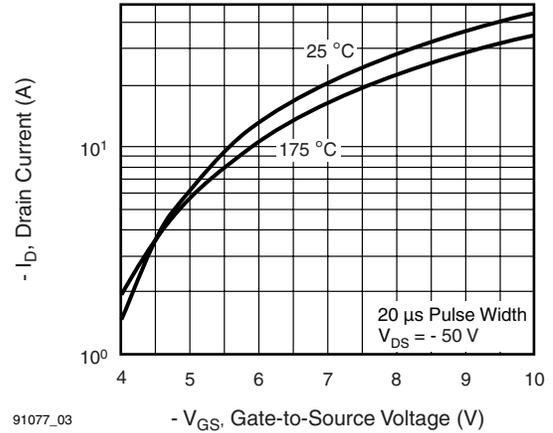
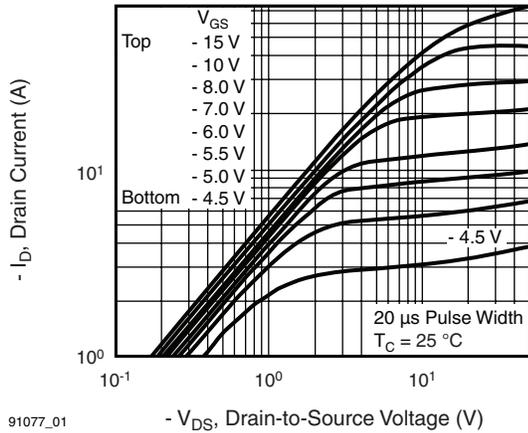
a. When mounted on 1" square PCB (FR-4 or G-10 material).

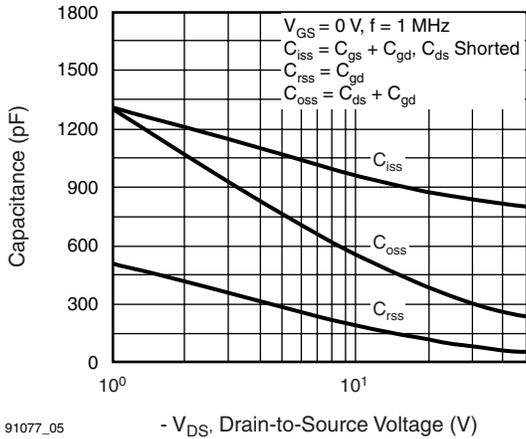
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX. UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		- 100	-	- V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$		-	- 0.10	- $^\circ\text{C/W}$	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		- 2.0	-	- 4.0 V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100\text{ nA}$	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$		-	-	- 100 μA	
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	- 500 μA	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -7.2\text{ A}^b$	-	-	0.30 Ω	
Forward Transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -7.2\text{ A}^b$		3.7	-	- S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	860	-	
Output Capacitance	C_{oss}			-	340	-	pF
Reverse Transfer Capacitance	C_{rss}			-	93	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}$	$I_D = -12\text{ A}, V_{DS} = -80\text{ V}$, see fig. 6 and 13 ^b	-	-	38	
Gate-Source Charge	Q_{GS}			-	-	6.8	nC
Gate-Drain Charge	Q_{GD}			-	-	21	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, I_D = -12\text{ A}, R_G = 12\text{ }\Omega, R_D = 3.9\text{ }\Omega$, see fig. 10 ^b		-	12	-	
Rise Time	t_r			-	52	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	31	-	
Fall Time	t_f			-	39	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	
Internal Source Inductance	L_S			-	7.5	-	nH
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	- 12	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	- 48	A
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -12\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	- 6.3 V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -12\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	120	240 ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.46	0.92 μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

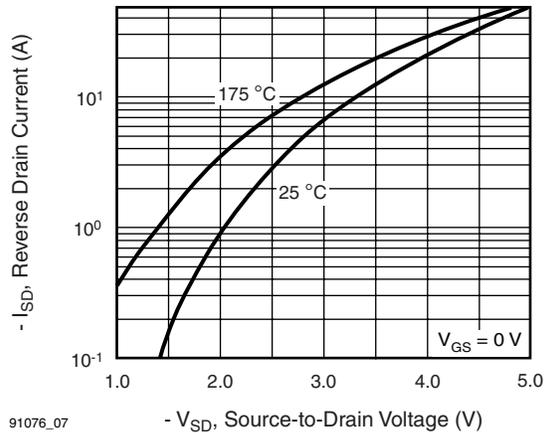
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





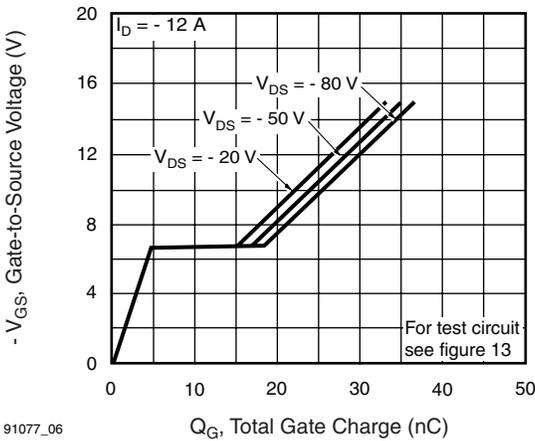
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



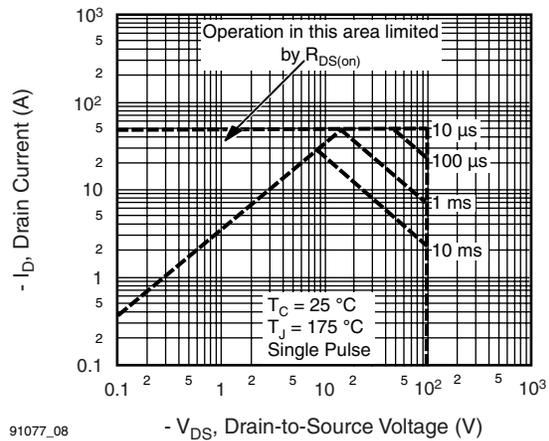
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



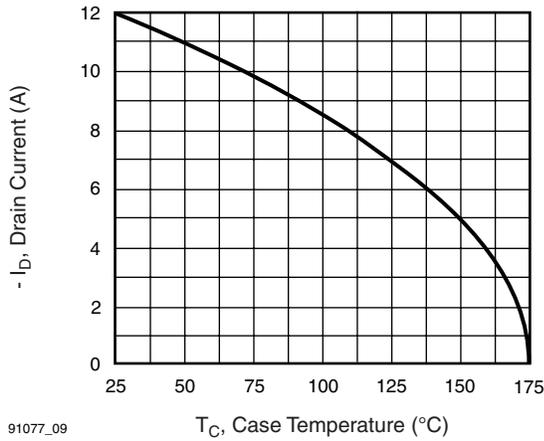
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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



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Fig. 8 - Maximum Safe Operating Area



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Fig. 9 - Maximum Drain Current vs. Case Temperature

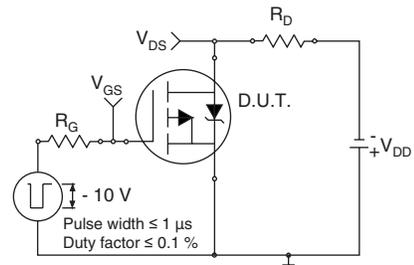


Fig. 10a - Switching Time Test Circuit

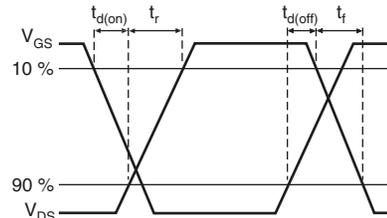
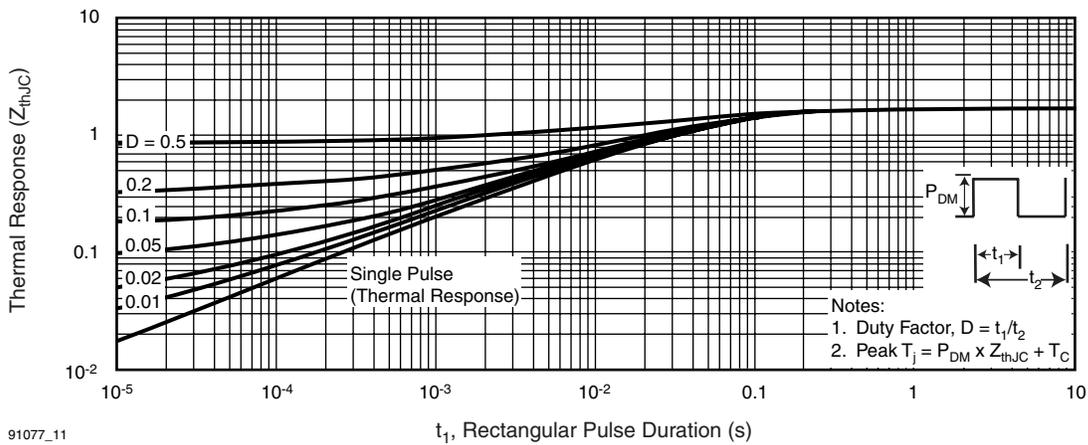


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

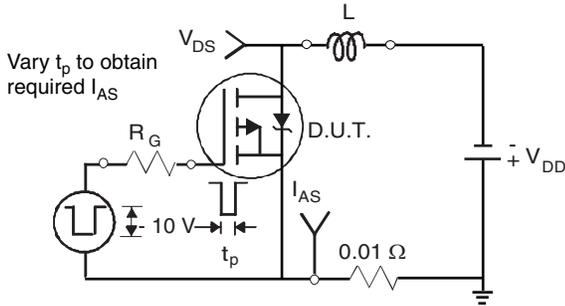


Fig. 12a - Unclamped Inductive Test Circuit

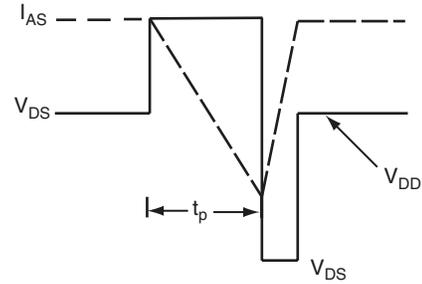


Fig. 12b - Unclamped Inductive Waveforms

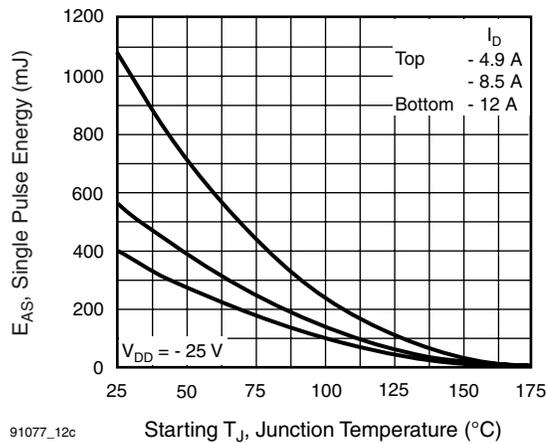


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

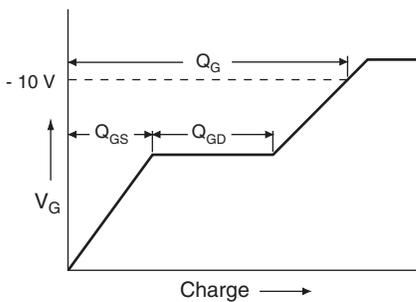


Fig. 13a - Basic Gate Charge Waveform

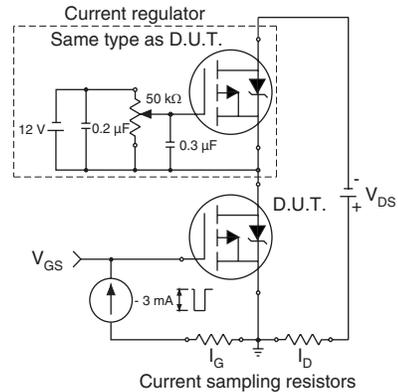
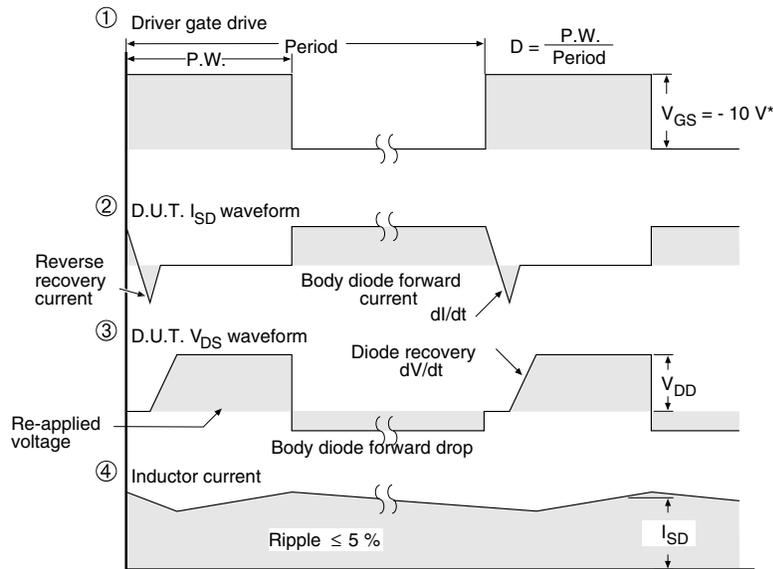
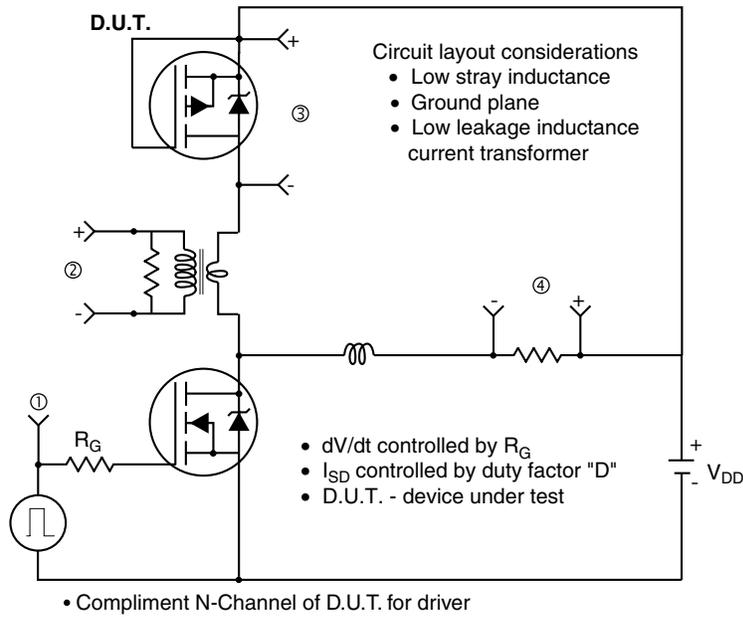


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5 V$ for logic level and $-3 V$ drive devices

Fig. 14 - For P-Channel

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